



2SJ76, 2SJ77, 2SJ78, 2SJ79

Silicon P Channel MOS FET

REJ03G0122-0200
(Previous: ADE-208-1179)
Rev.2.00
Sep 07, 2005

Description

High frequency and low frequency power amplifier, high speed power switching

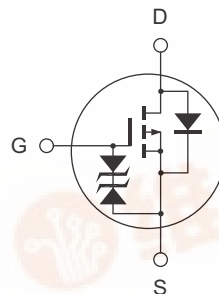
Complementary pair with 2SK213, 2SK214, 2SK215, 2SK216

Features

- Suitable for direct mounting
- High forward transfer admittance
- Excellent frequency response
- Enhancement-mode

Outline

RENESAS Package code: PRSS0004AC-A
(Package name: TO-220AB)



1. Gate
2. Source (Flange)
3. Drain

Absolute Maximum Ratings

(Ta = 25°C)

Item		Symbol	Value	Unit
Drain to source voltage	2SJ76	V_{DSX}	-140	V
	2SJ77		-160	
	2SJ78		-180	
	2SJ79		-200	
Gate to source voltage		V_{GSS}	±15	V
Drain current		I_D	-500	mA
Body to drain diode reverse drain current		I_{DR}	-500	mA
Channel dissipation	P_{ch}		1.75	W
	$P_{ch}^{Note\ 1}$		30	W
Channel temperature		T_{ch}	150	°C
Storage temperature		T_{stg}	-45 to +150	°C

Note: 1. Value at Tc = 25°C

Electrical Characteristics

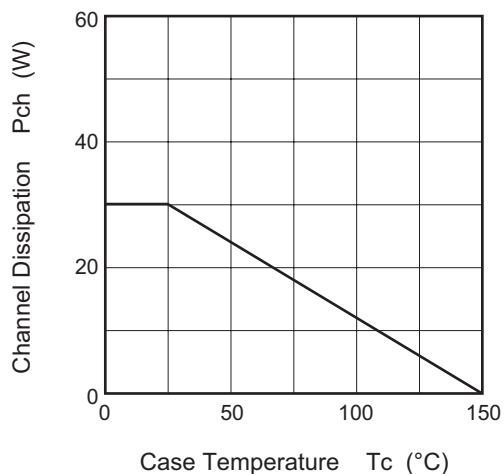
(Ta = 25°C)

Item		Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	2SJ76	$V_{(BR)DSX}$	-140	—	—	V	$V_{GS} = 2\text{ V}, I_D = -1\text{ mA}$
	2SJ77		-160	—	—	V	
	2SJ78		-180	—	—	V	
	2SJ79		-200	—	—	V	
Gate to source breakdown voltage		$V_{(BR)GSS}$	±15	—	—	V	$I_G = \pm 10\text{ }\mu\text{A}, V_{DS} = 0$
Gate to source cutoff voltage		$V_{GS(on)}$	-0.2	—	-1.5	V	$I_D = -10\text{ mA}, V_{DS} = -10\text{ V}^{Note\ 2}$
Drain to source saturation voltage		$V_{DS(sat)}$	—	—	-2.0	V	$I_D = -10\text{ mA}, V_{GS} = 0^{Note\ 2}$
Forward transfer admittance		$ y_{fs} $	20	35	—	mS	$I_D = -10\text{ mA}, V_{DS} = -20\text{ V}^{Note\ 2}$
Input capacitance		C_{iss}	—	120	—	pF	$V_{DS} = -10\text{ V}, I_D = -10\text{ mA},$ $f = 1\text{ MHz}$
Reverse transfer capacitance		C_{rss}	—	4.8	—	pF	

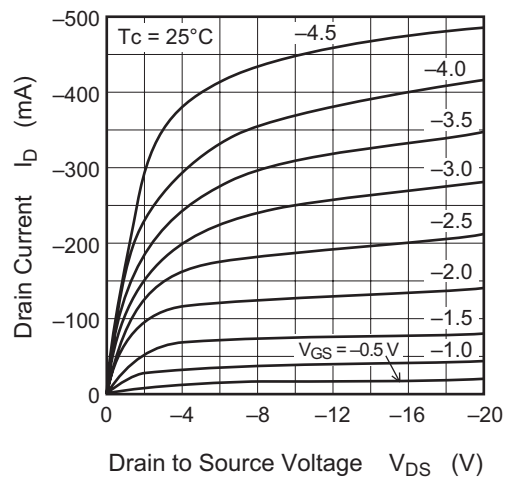
Note: 2. Pulse test

Main Characteristics

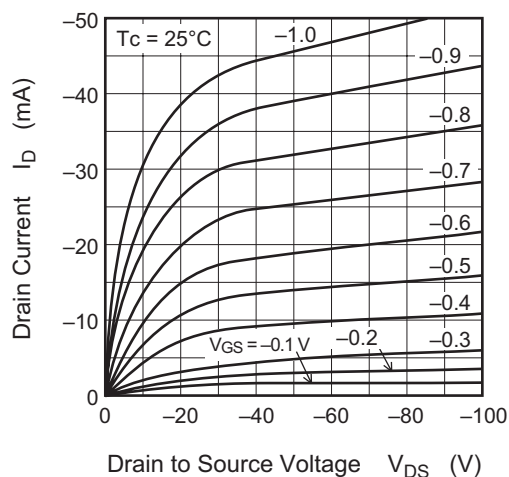
Power vs. Temperature Derating



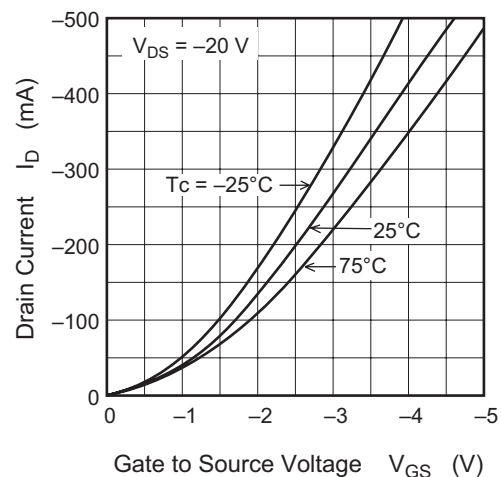
Typical Output Characteristics



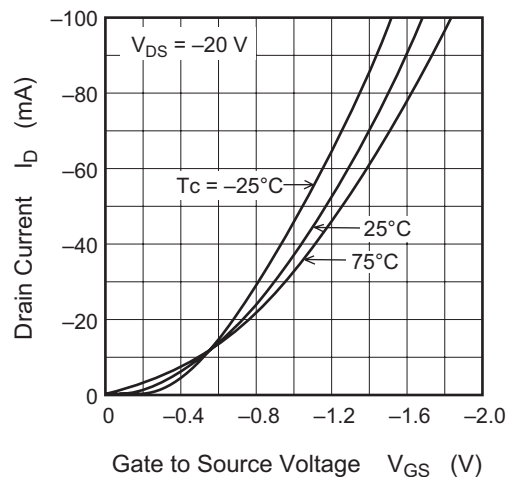
Typical Output Characteristics



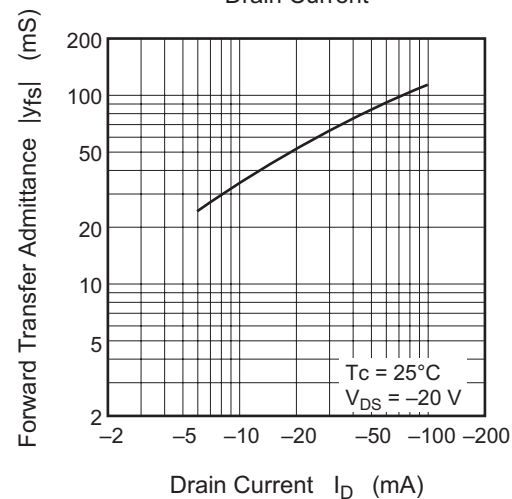
Typical Transfer Characteristics

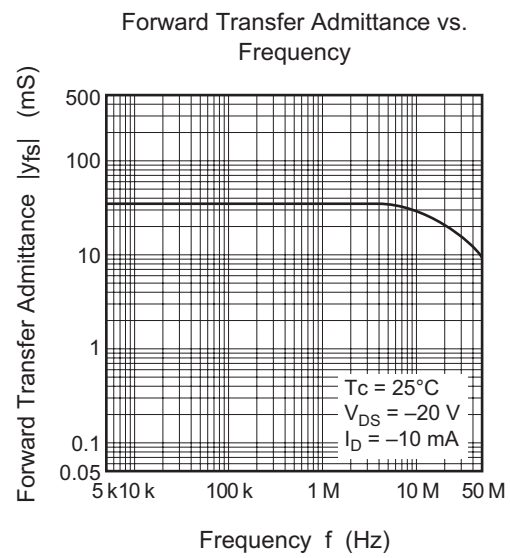


Typical Transfer Characteristics

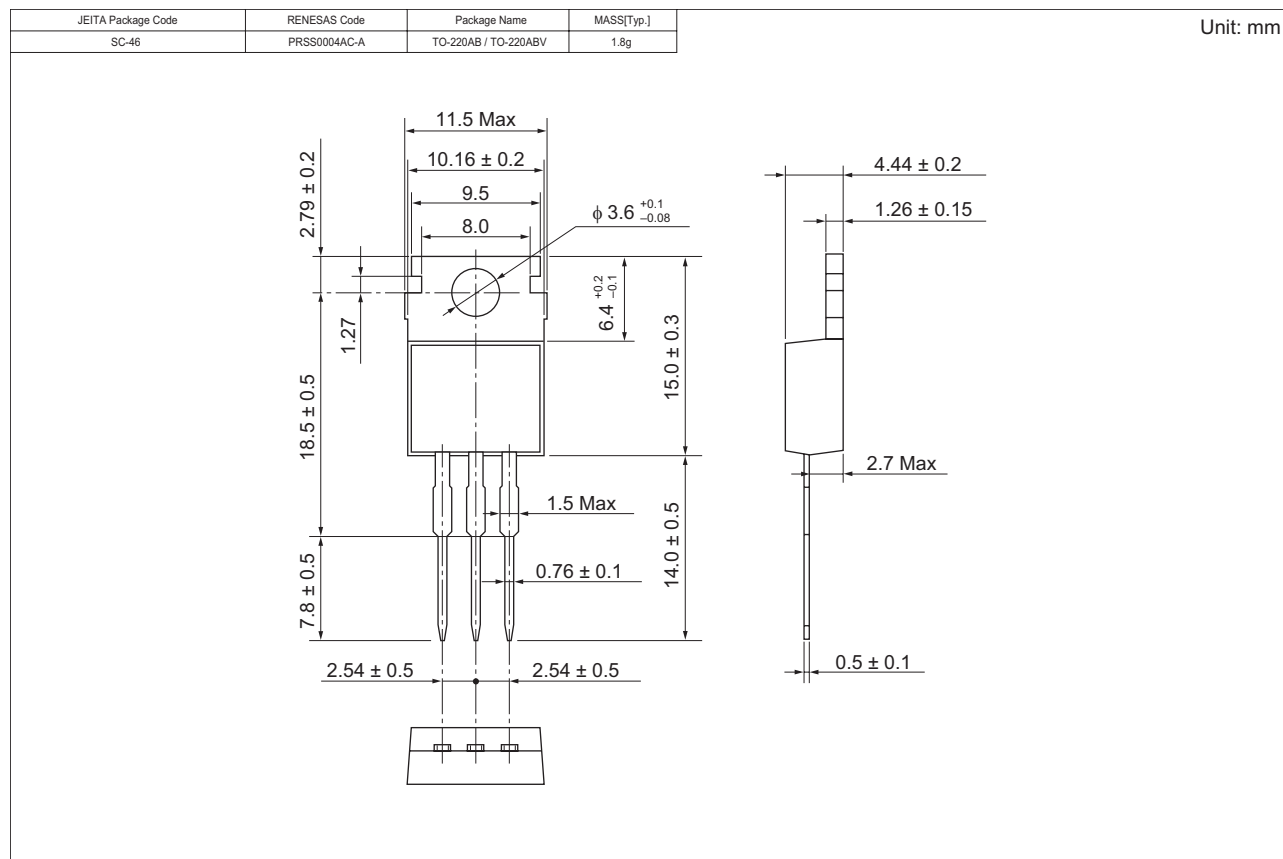


Forward Transfer Admittance vs. Drain Current





Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
2SJ76-E	500 pcs	Box (Sack)
2SJ77-E	500 pcs	Box (Sack)
2SJ78-E	500 pcs	Box (Sack)
2SJ79-E	500 pcs	Box (Sack)

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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Renesas Technology America, Inc.

450 Holger Way, San Jose, CA 95134-1368, U.S.A
Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited

Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology Hong Kong Ltd.

7th Floor, North Tower, World Finance Centre, Harbour City, 1 Canton Road, Tsimshatsui, Kowloon, Hong Kong
Tel: <852> 2265-6688, Fax: <852> 2730-6071

Renesas Technology Taiwan Co., Ltd.

10th Floor, No.99, Fushing North Road, Taipei, Taiwan
Tel: <886> (2) 2715-2888, Fax: <886> (2) 2713-2999

Renesas Technology (Shanghai) Co., Ltd.

Unit2607 Ruijing Building, No.205 Maoming Road (S), Shanghai 200020, China
Tel: <86> (21) 6472-1001, Fax: <86> (21) 6415-2952

Renesas Technology Singapore Pte. Ltd.

1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632
Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd.

Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea
Tel: <82> 2-796-3115, Fax: <82> 2-796-2145

Renesas Technology Malaysia Sdn. Bhd.

Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jalan Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia
Tel: <603> 7955-9390, Fax: <603> 7955-9510